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8-Bit Shift Register with Output Storage Register (3-State)

The MC74VHC595 is an advanced high speed 8-bit shift register with an output storage register fabricated with silicon gate CMOS technology.

It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC595 contains an 8-bit static shift register which feeds an 8-bit storage register.

Shift operation is accomplished on the positive going transition of the Shift Clock input (SCK). The output register is loaded with the contents of the shift register on the positive going transition of the Register Clock input (RCK). Since the RCK and SCK signals are independent, parallel outputs can be held stable during the shift operation. And, since the parallel outputs are 3–state, the VHC595 can be directly connected to an 8–bit bus. This register can be used in serial–to–parallel conversion, data receivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

Features

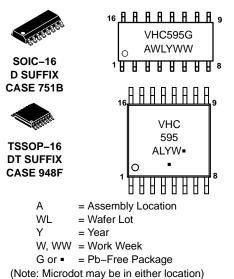
- High Speed: $f_{max} = 185$ MHz (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 1.0 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



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MARKING DIAGRAMS



PIN ASSIGNMENT

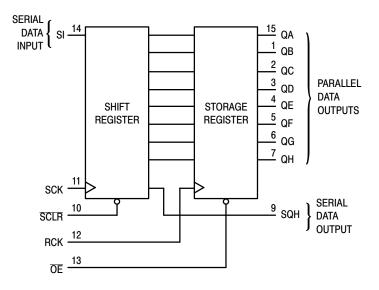
QB [1 •	16	
QC [2	15] QA
QD [3	14] si
QE [4	13	
QF [5	12] вск
QG [6	11] ѕск
QH [7	10	
GND [8	9] ѕон

ORDERING INFORMATION

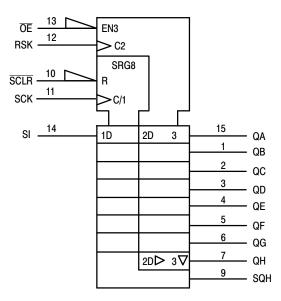
Device	Package	Shipping [†]
MC74VHC595DR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74VHC595DTR2G, NLV74VHC595DTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

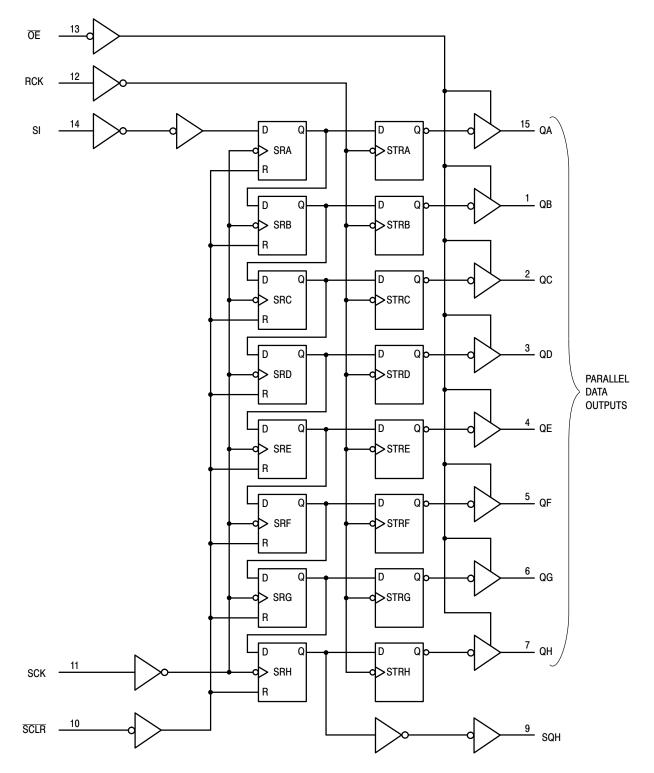




IEC LOGIC SYMBOL



EXPANDED LOGIC DIAGRAM



FUNCTION	TABLE
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			Inputs			Resulting Function					
Operation	Reset (SCLR)	Serial Input (SI)	Shift Clock (SCK)	Reg Clock (RCK)	Output Enable (OE)	Shift Register Contents	Storage Register Contents	Serial Output (SQH)	Parallel Outputs (QA – QH)		
Clear shift register	L	Х	Х	L, H, ↓	L	L	U	L	U		
Shift data into shift register	Н	D	↑	L, H, ↓	L	$D \rightarrow SR_A;$ $SR_N \rightarrow SR_{N+1}$	U	$SR_G \rightarrow SR_H$	U		
Registers remains unchanged	Н	Х	L, H, ↓	х	L	U	**	U	**		
Transfer shift register contents to storage register	Н	Х	L, H, ↓	↑	L	U	SR _N →STR _N	*	SR _N		
Storage register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U		
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled		
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z		

STR = storage register contents U = remains unchanged

 $\uparrow = Low - to - High$

* = depends on Reset and Shift Clock inputs
** = depends on Register Clock input

MAXIMUM RATINGS*

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		– 0.5 to + 7.0	V
V _{in}	DC Input Voltage		– 0.5 to + 7.0	V
Vout	DC Output Voltage		-0.5 to V_CC + 0.5	V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current		± 20	mA
I _{out}	DC Output Current, per Pin		± 25	mA
Icc	DC Supply Current, V_{CC} and GN	ID Pins	± 50	mA
P _D	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		– 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{in}	DC Input Voltage		0	5.5	V
V _{out}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature, All Package	lypes	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.3V ±0.3V V _{CC} =5.0V ±0.5V	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

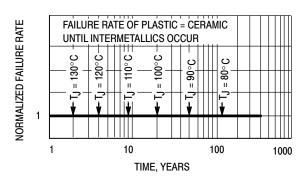


Figure 1. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

			Vcc		T _A = 25°C	;	$T_A = \le 85^{\circ}C$		T _A = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65		0.59 0.9 1.35 1.65	V
V _{OH}	$\begin{array}{l} \mbox{Minimum High-Level} \\ \mbox{Output Voltage} \\ \mbox{V}_{\rm IN} = \mbox{V}_{\rm IH} \mbox{ or } \mbox{V}_{\rm IL} \end{array}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu \text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low–Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5 V \text{ or GND}$	0 to 5.5			± 0.1		± 1.0		± 1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μA
I _{OZ}	Three–State Output Off–State Current		5.5			± 0.25		± 2.5		± 2.5	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

Devenueter		T _A = 25°		~		T _A = ≤ 85°C		T _A = ≤ 125°C		
Parameter	eter Test Conditions		Min	Тур	Max	Min	Max	Min	Max	Unit
Maximum Clock Frequency (50%	V_{CC} = 3.3 \pm 0.3 V		80	150		70		70		MHz
Duty Cycle)	$V_{CC}=5.0\pm0.5~V$		135	185		115		115		
Propagation Delay, SCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		8.8 11.3	13.0 16.5	1.0 1.0	15.0 18.5	1.0 1.0	15.0 18.5	ns
SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		6.2 7.7	8.2 10.2	1.0 1.0	9.4 11.4	1.0 1.0	9.4 11.4	
Propagation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		8.4 10.9	12.8 16.3	1.0 1.0	13.7 17.2	1.0 1.0	13.7 17.2	ns
CPLR to SQH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.9 7.4	8.0 10.0	1.0 1.0	9.1 11.1	1.0 1.0	9.1 11.1	
Propagation Delay, RCK to	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		7.7 10.2	11.9 15.4	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
QA–QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15pF$ $C_L = 50pF$		5.4 6.9	74 9.4	1.0 1.0	8.5 10.5	1.0 1.0	8.5 10.5	
Output Enable Time,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	$C_L = 15pF$ $C_L = 50pF$		7.5 9.0	11.5 15.0	1.0 1.0	13.5 17.0	1.0 1.0	13.5 17.0	ns
OE to QA–QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	$C_L = 15pF$ $C_L = 50pF$		4.8 8.3	8.6 10.6	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	
Output Disable Time,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C _L = 50pF		12.1	15.7	1.0	16.2	1.0	16.2	ns
OE to QA–QH	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $R_{L} = 1 \text{ k}\Omega$	C _L = 50pF		7.6	10.3	1.0	11.0	1.0	11.0	
Input Capacitance				4	10		10		10	pF
Three–State Output Capacitance (Output in High–Impedance State), QA–QH				6			10		10	pF
	Frequency (50% Duty Cycle) Propagation Delay, SCK to SQH Propagation Delay, CPLR to SQH Propagation Delay, RCK to QA–QH Output Enable Time, OE to QA–QH Output Disable Time, OE to QA–QH Input Capacitance Three–State Output in High–Impedance	$\begin{array}{c c} Frequency (50\% \\ Duty Cycle) \end{array} \qquad \begin{array}{c} V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 3.3 \pm 0.3 \ V \\ \hline V_{CC} = 3.3 \pm 0.3 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline Output Enable \\ Time, \\ \overline{OE} to \ QA-QH} \qquad \begin{array}{c} V_{CC} = 3.3 \pm 0.3 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline R_L = 1 \ k\Omega \\ \hline R_L = 1 \ k$	$ \begin{array}{c} \mbox{Frequency (50\%} \\ \mbox{Duty Cycle)} & V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline V_{CL} = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 15 \ P \\ C_L = 50 \ F \\ \hline V_{CC} = 5.0 \pm 0.5 \ V \\ \hline C_L = 50 \ F \\ \hline C_L = 50 \ F$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$

		Typical @ 25°C, $V_{CC} = 5.0V$		
C _{PD}	Power Dissipation Capacitance (Note 1)	87	pF	
1 Copis	defined as the value of the internal equivalent canacitance which is calculated from th	e operating current consumption witho	ut load	

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

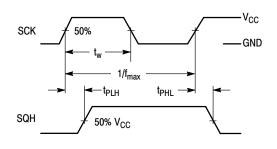
NOISE CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns, C_L = 50pF, V_{CC} = 5.0V)

		T _A =	25°C	
Symbol	Characteristic	Тур	Мах	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.8	1.0	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.8	- 1.0	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

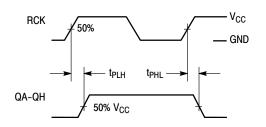
TIMING REQUIREMENTS (Input $t_r = t_f = 3.0$ ns)

		V _{cc}	T _A =	25°C	T _A = − 40 to 85°C	T _A = - 55 to 125°C	
Symbol	Parameter	V	Тур	Limit	Limit	Limit	Unit
t _{su}	Setup Time, SI to SCK	3.3 5.0		3.5 3.0	3.5 3.0	3.5 3.0	ns
t _{su(H)}	Setup Time, SCK to RCK	3.3 5.0		8.0 5.0	8.5 5.0	8.5 5.0	ns
t _{su(L)}	Setup Time, SCLR to RCK	3.3 5.0		8.0 5.0	9.0 5.0	9.0 5.0	ns
t _h	Hold Time, SI to SCK	3.3 5.0		1.5 2.0	1.5 2.0	1.5 2.0	ns
t _{h(L)}	Hold Time, SCLR to RCK	3.3 5.0		0 0	0 0	1.0 1.0	ns
t _{rec}	Recovery Time, SCLR to SCK	3.3 5.0		3.0 2.5	3.0 2.5	3.0 2.5	ns
t _w	Pulse Width, SCK or RCK	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns
t _{w(L)}	Pulse Width, SCLR	3.3 5.0		5.0 5.0	5.0 5.0	5.0 5.0	ns

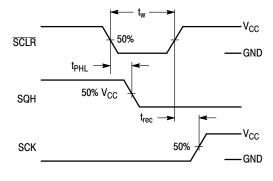
SWITCHING WAVEFORMS













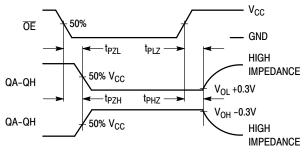
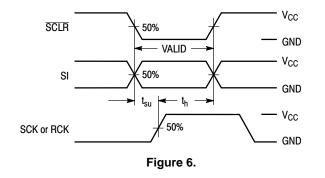
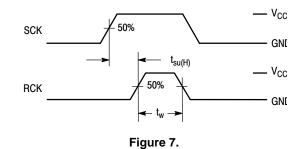
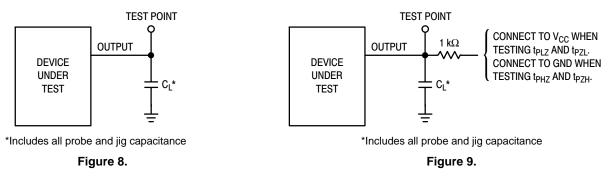


Figure 5.

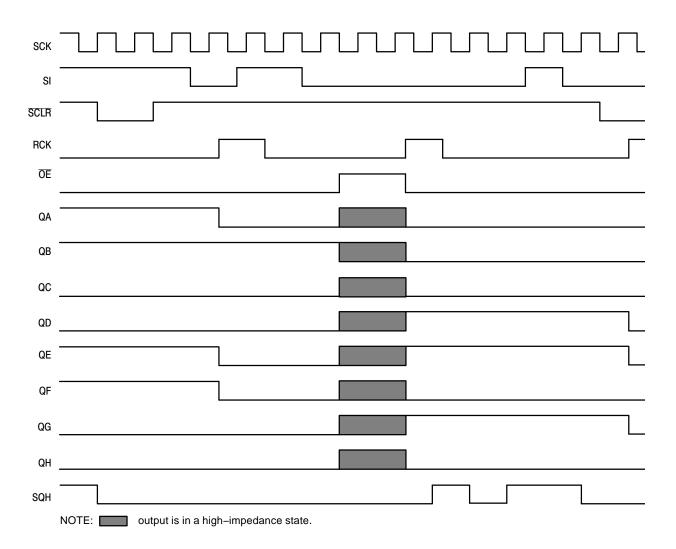




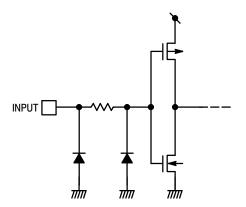
TEST CIRCUITS



TIMING DIAGRAM

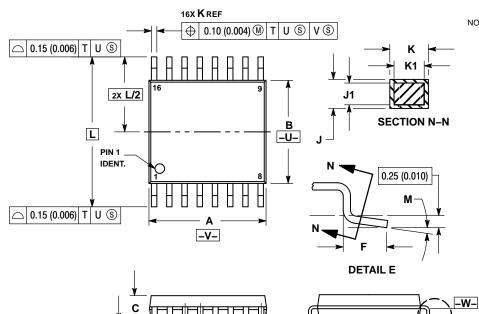


INPUT EQUIVALENT CIRCUIT



PACKAGE DIMENSIONS





G

○ 0.10 (0.004) -T- SEATING PLANE

D

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. NOTE LAOU OF OUTED CHAIN NOT

FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR

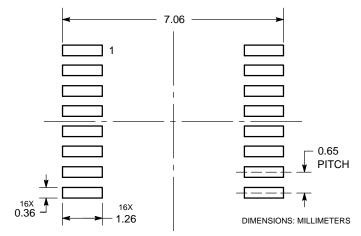
REFERENCE ONLY.
DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

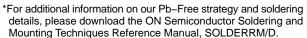
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
ĸ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*

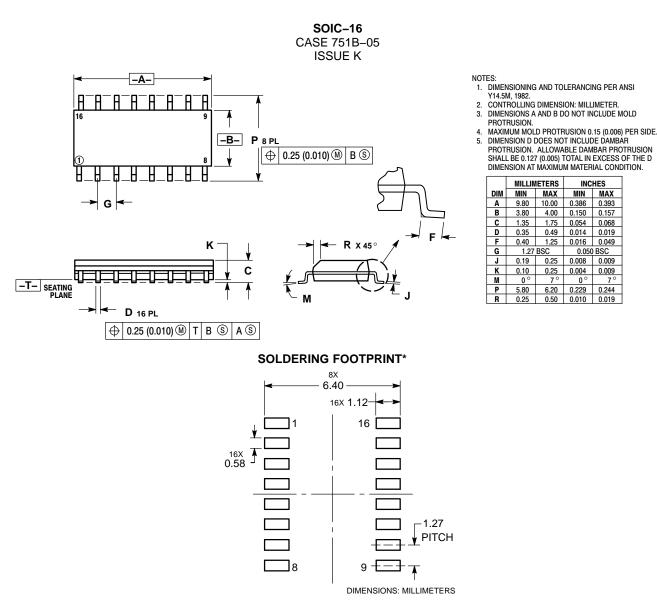
DETAIL E

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PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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MILLIMETERS

MIN MAX

10.00

4.00

1.25

7 °

1.75 0.054

9.80

3.80

1.35

0.35

0.40

0.19

0.10

0°

5.80 0.25

1 27 BSC

INCHES

0.150 0.157

0.016 0.049

0.050 BSC 0.25 0.008 0.009

0.386

0.49 0.014 0.019

0.25 0.004 0.009

6.20 0.229 0.244

0.50 0.010 0.019

0 °

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0.393

0.068

7°

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